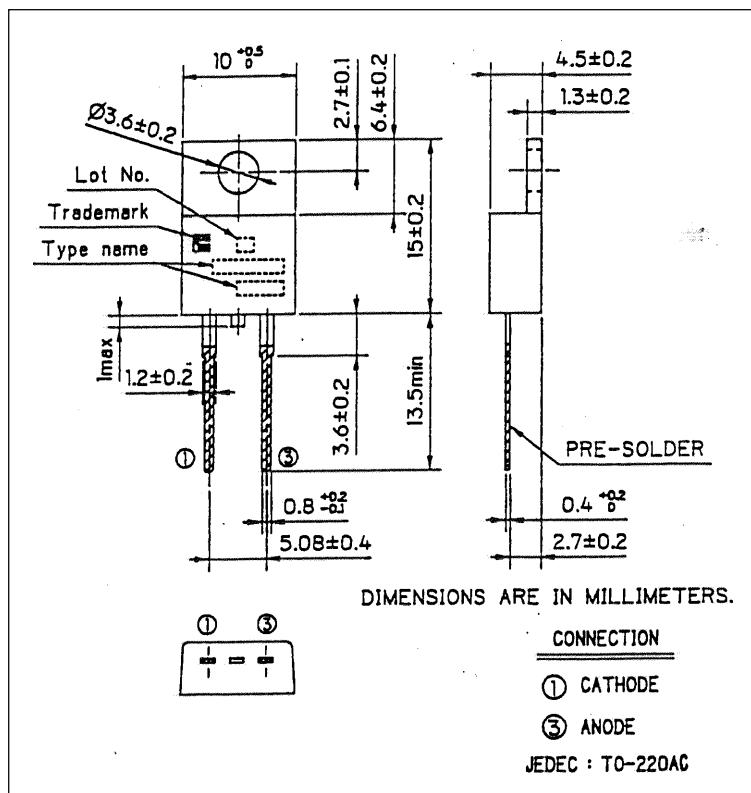
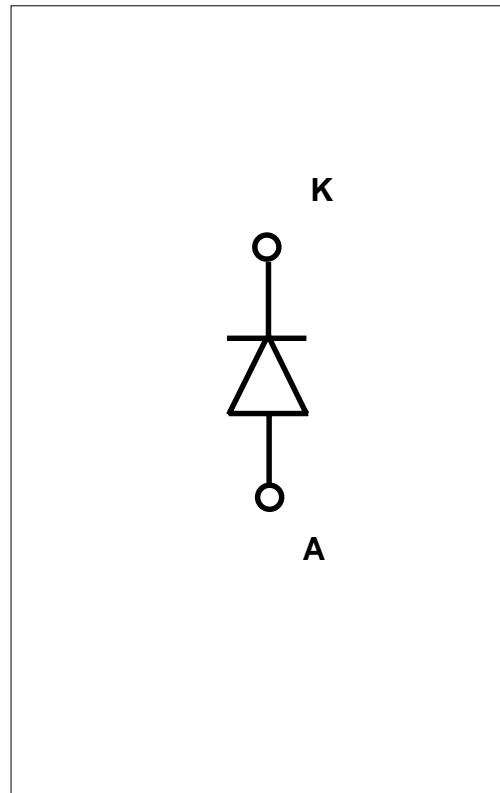


## Fast Recovery Diode for IGBT

### ■ Outline Drawings Units mm



### ■ Equivalent circuit



### ■ Maximum ratings and characteristics

#### ● Absolute maximum ratings ( $T_c=25^\circ\text{C}$ )

Item	Symbol	Test Conditions	Ratings	Units
Repetitive Reverse Voltage	$V_{RRM}$		1200	V
Repetitive peak surge current	$I_{FM}$	20kHz Duty 50% Squ. wave	$T_c=127^\circ\text{C}$	5
			$T_c=25^\circ\text{C}$	18
Average rectified forward current	$I_{F(A)}$	DC	5	A
Non-repetitive peak surge current	$I_{FSM}$	Pulse 10ms, sin. wave	50	A
Maximam Power Dissipaion	$P_o$		35	W
Operating Temperature	$T_j$		+150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$		-40 to +150	$^\circ\text{C}$
Mounting Screw Torque			50	N-cm

#### ● Electrical characteristics (at $T_c=25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Test Conditions	Max	Units
Reverse Current	$I_R$	$V_R = 1200\text{V}$	1.0	mA
Forward voltage	$V_{FM}$	$I_F = 5\text{A}$	3.0	V
Reverse recovery time	$t_{rr}$	$I_F = 5\text{A}, V_R=200\text{V}, di/dt=100\text{A}/\mu\text{s}$	0.3	$\mu\text{s}$

#### ● Thermal resistance characteristics

Item	Symbol	Test Conditions	Max	Units
Thermal resistance	$R_{th(j-c)}$	junction to case	4.16	$^\circ\text{C}/\text{W}$

## ■ Characteristics

